



# STB160N75F3 STP160N75F3 - STW160N75F3

N-channel 75V - 3.5mΩ - 120A - TO-220 - TO-247 - D<sup>2</sup>PAK  
MDmesh™ low voltage Power MOSFET

TARGET SPECIFICATION

## General features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB160N75F3	75V	4.2mΩ	120A <sup>(1)</sup>
STP160N75F3	75V	4.5mΩ	120A <sup>(1)</sup>
STW160N75F3	75V	4.5mΩ	120A <sup>(1)</sup>

1. Current limited by package

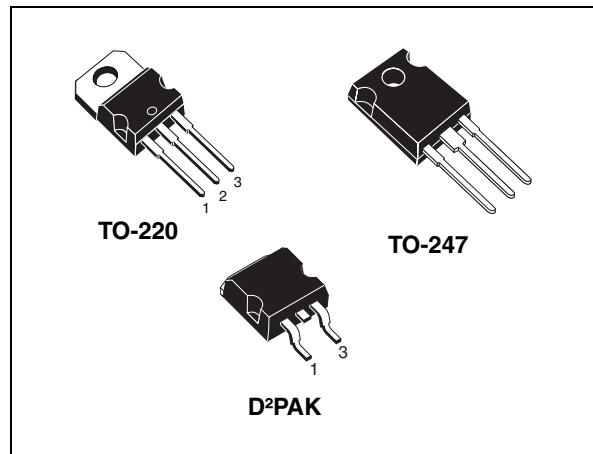
- Ultra low on-resistance
- 100% Avalanche tested

## Description

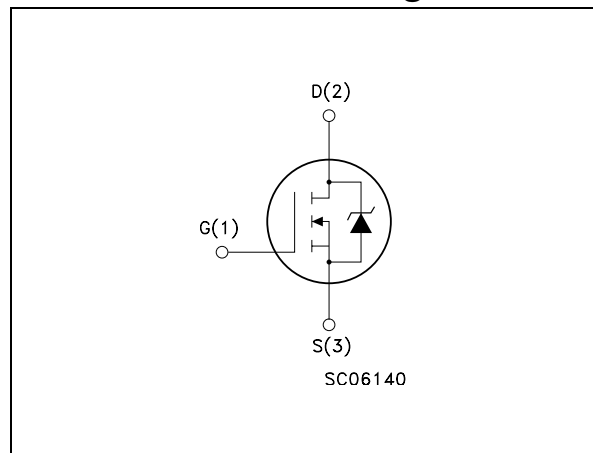
This N-channel enhancement mode Power MOSFET is the latest refinement of STMicroelectronics unique “Single Feature Size™” strip-based process with less critical alignment steps and therefore a remarkable manufacturing reproducibility. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and low gate charge.

## Applications

- Switching application



## Internal schematic diagram



## Order codes

Part number	Marking	Package	Packaging
STB160N75F3	160N75F3	D <sup>2</sup> PAK	Tape & reel
STP160N75F3	160N75F3	TO-220	Tube
STW160N75F3	160N75F3	TO-247	Tube

## Contents

1	Electrical ratings .....	3
2	Electrical characteristics .....	4
3	Test circuit .....	6
4	Package mechanical data .....	7
5	Packaging mechanical data .....	11
6	Revision history .....	12

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	75	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	96	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
$P_{TOT}^{(3)}$	Total dissipation at $T_C = 25^\circ\text{C}$	315	W
	Derating factor	2.1	W/ $^\circ\text{C}$
dv/dt	Peak diode recovery voltage slope	Tbd	V/ns
$E_{AS}$	Single pulse avalanche energy	Tbd	mJ
$T_j$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Current limited by package
2. Pulse width limited by safe operating area
3. Rated according to Rthj-case

**Table 2. Thermal resistance**

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case max	0.48	$^\circ\text{C}/\text{W}$
Rthj-amb	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	75			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, @ 125^{\circ}C$			10 100	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20V$			$\pm 200$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 60A$		3.5 3.2	4.5 4.2	$m\Omega$ $m\Omega$

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 4.5A$ $I_D = 10A$		Tbd		S
$C_{iss}$	Input capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		7000		pF
$C_{oss}$	Output capacitance			1100		pF
$C_{rss}$	Reverse transfer capacitance			32		pF
$Q_g$	Total gate charge	$V_{DD} = 44V, I_D = 60A$		110	Tbd	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10V$		Tbd		nC
$Q_{gd}$	Gate-drain charge	(see Figure 2)		Tbd		nC

1. Pulsed: pulse duration = 300 $\mu s$ , duty cycle 1.5%

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=35\text{ V}$ , $I_D=60\text{ A}$ , $R_G=4.7\Omega$ , $V_{GS}=10\text{ V}$ , (see Figure 4)		Tbd		ns
$t_r$	Rise time			Tbd		ns
$t_{d(off)}$	Turn-off delay time			Tbd		ns
$t_f$	Fall time			Tbd		ns

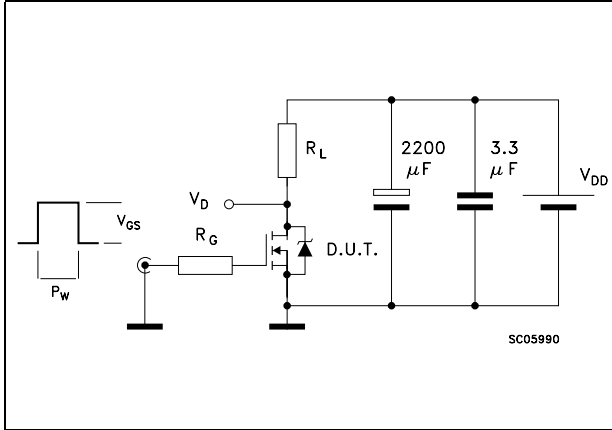
**Table 6. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=120\text{ A}$ , $V_{GS}=0$			1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD}=120\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=30\text{ V}$ , $T_j=150^\circ\text{C}$ (see Figure 3)		75		ns
$Q_{rr}$	Reverse recovery charge			195		nC
$I_{RRM}$	Reverse recovery current			5		A

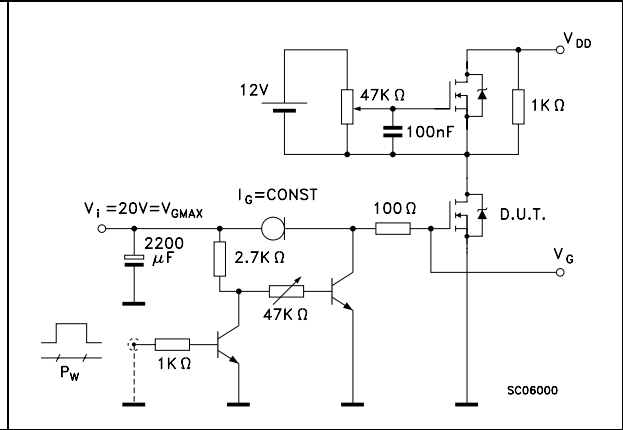
1. Pulse with limited by safe operating area
2. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

### 3 Test circuit

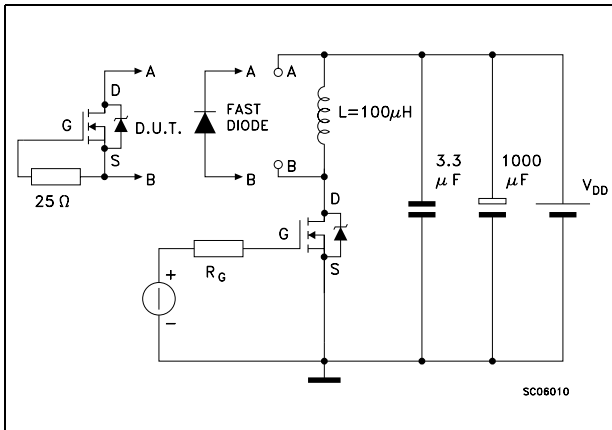
**Figure 1. Switching times test circuit for resistive load**



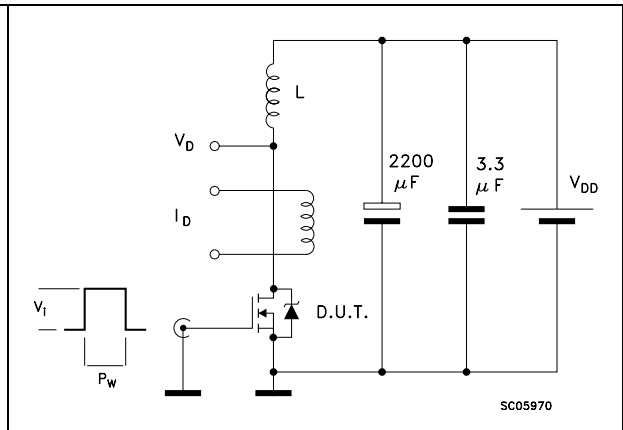
**Figure 2. Gate charge test circuit**



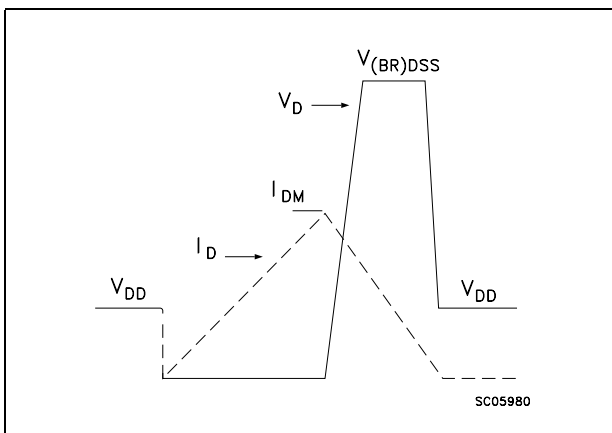
**Figure 3. Test circuit for inductive load switching and diode recovery times**



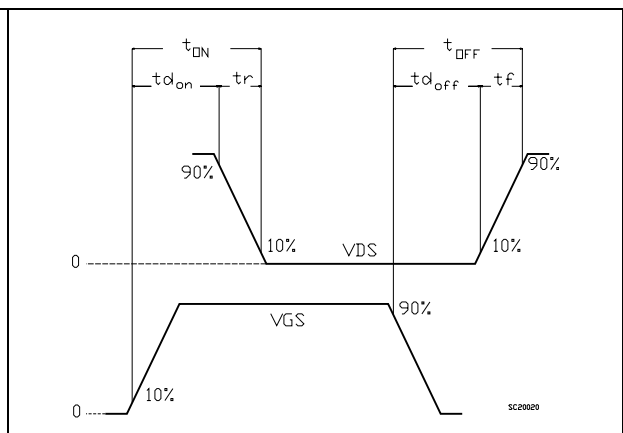
**Figure 4. Unclamped inductive load test circuit**



**Figure 5. Unclamped inductive waveform**



**Figure 6. Switching time waveform**

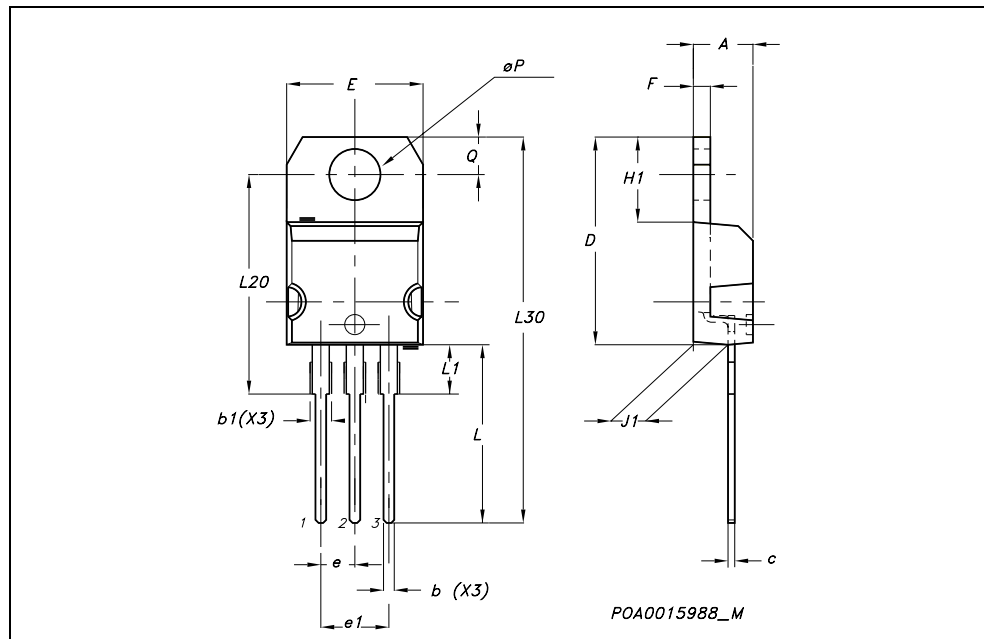


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

**TO-220 MECHANICAL DATA**

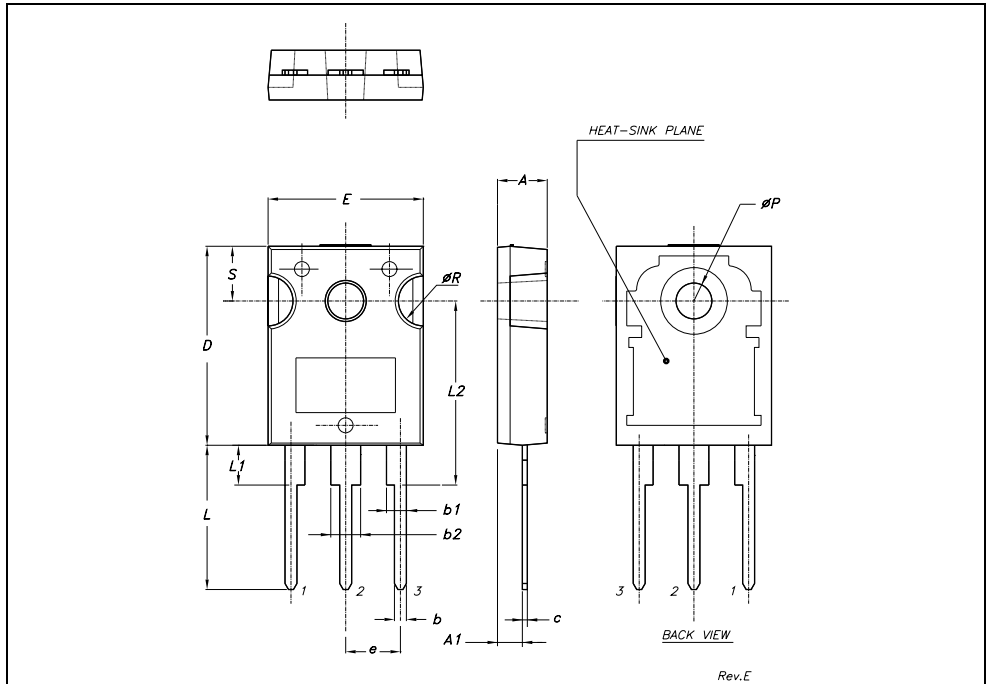
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116





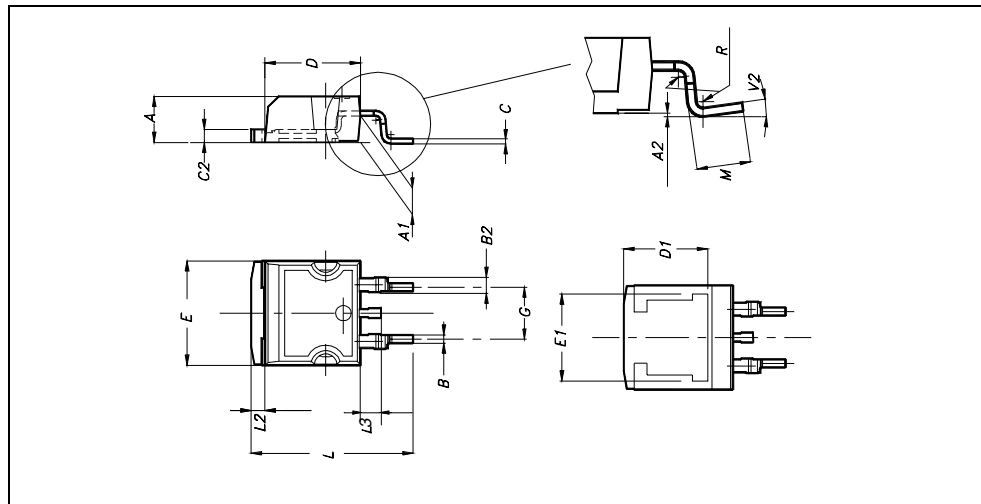
**TO-247 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



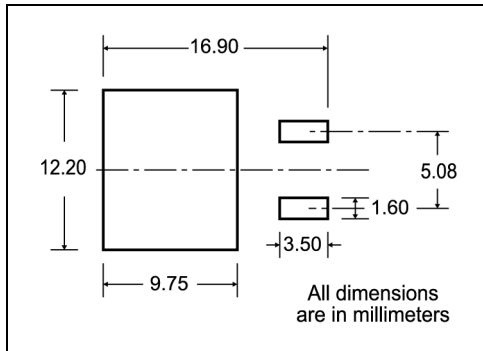
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

### TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

### REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

TRL

FEED DIRECTION

Bending radius R min.

\* on sales type

## 6 Revision history

Table 7. Revision history

Date	Revision	Changes
07-Feb-2007	1	First release

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